

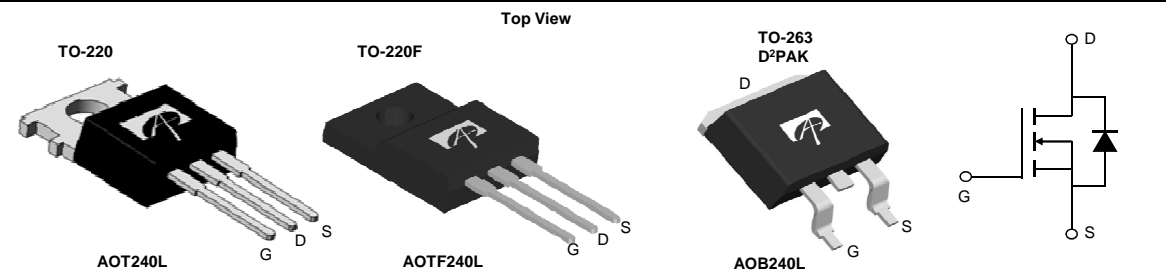
**General Description**

The AOT240L & AOB240L & AOTF240L uses Trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. Power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $C_{rss}$ .

**Product Summary**

$V_{DS}$	40V
$I_D$ (at $V_{GS}=10V$ )	105A/85A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 2.9m $\Omega$ (< 2.6m $\Omega^*$ )
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 3.7m $\Omega$ (< 3.5m $\Omega^*$ )

100% UIS Tested  
 100%  $R_g$  Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT240L	TO-220	Tube	1000
AOB240L	TO-263	Tape & Reel	800
AOTF240L	TO-220F	Tube	1000

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	AOT240L/AOB240L	AOTF240L	Units
Drain-Source Voltage	$V_{DS}$	40		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		V
Continuous Drain Current <sup>G</sup>	$T_C=25^\circ\text{C}$	105	85	A
	$T_C=100^\circ\text{C}$	82	60	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	400		A
Continuous Drain Current	$T_A=25^\circ\text{C}$	20		A
	$T_A=70^\circ\text{C}$	16		
Avalanche Current <sup>C</sup>	$I_{AS}$	68		A
Avalanche energy $L=0.1\text{mH}$ <sup>C</sup>	$E_{AS}$	231		mJ
Power Dissipation <sup>B</sup>	$T_C=25^\circ\text{C}$	176	41	W
	$T_C=100^\circ\text{C}$	88	20	
Power Dissipation <sup>A</sup>	$T_A=25^\circ\text{C}$	1.9		W
	$T_A=70^\circ\text{C}$	1.2		
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 175		$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	AOT240L/AOB240L	AOTF240L	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	15	15	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient <sup>A,D</sup>		65	65	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.85	3.6	$^\circ\text{C}/\text{W}$

\* Surface mount package TO263

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	40			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.7	2.2	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	400			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A TO220/TO220F T <sub>J</sub> =125°C		2.4 3.7	2.9 4.7	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A TO220/TO220F		3	3.7	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =20A TO263		2.1	2.6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A TO263		2.7	3.5	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		78		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.65	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current <sup>G</sup>				105	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =20V, f=1MHz		3510		pF
C <sub>OSS</sub>	Output Capacitance			1070		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			68		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.5	1	1.5	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =20V, I <sub>D</sub> =20A		49	72	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			22	32	nC
Q <sub>gs</sub>	Gate Source Charge			9		nC
Q <sub>gd</sub>	Gate Drain Charge			7		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =20V, R <sub>L</sub> =1Ω, R <sub>GEN</sub> =3Ω		11		ns
t <sub>r</sub>	Turn-On Rise Time			10		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			38		ns
t <sub>f</sub>	Turn-Off Fall Time			11		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, di/dt=500A/μs		21		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, di/dt=500A/μs		58		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=175° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

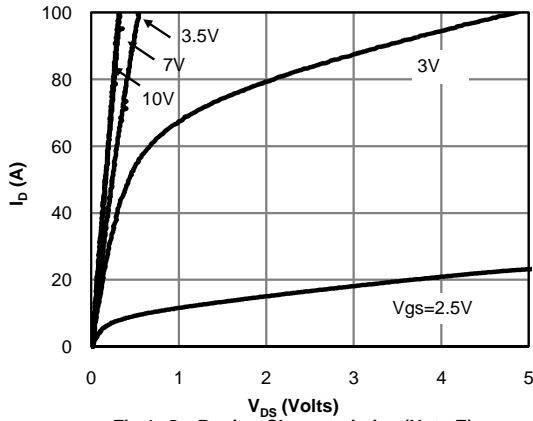
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=175° C. The SOA curve provides a single pulse rating.

G. The maximum current limited by package.

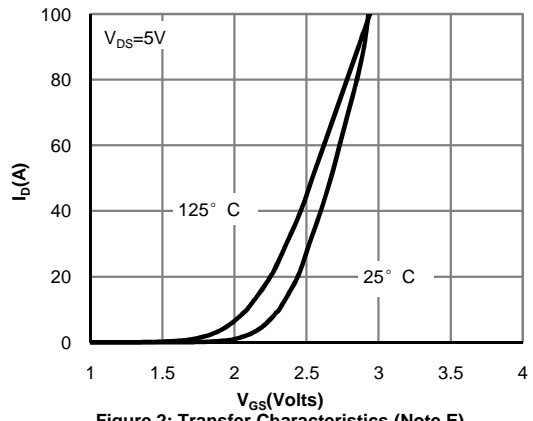
H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

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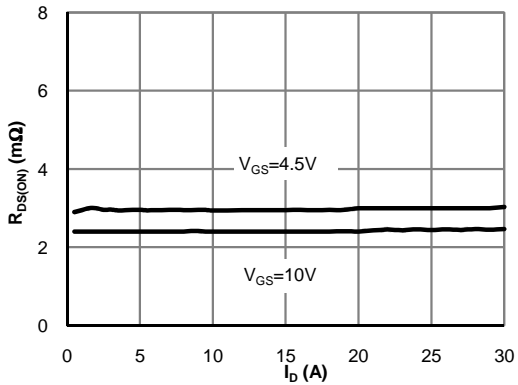
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



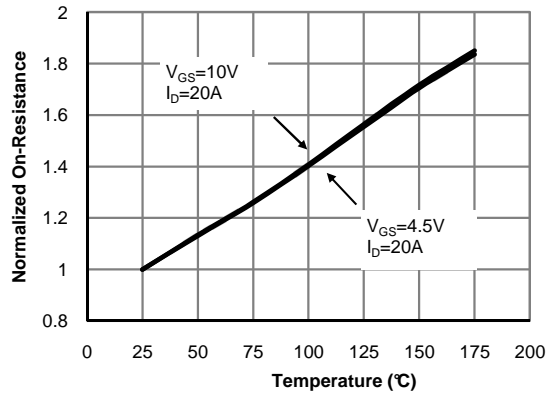
**Fig 1: On-Region Characteristics (Note E)**



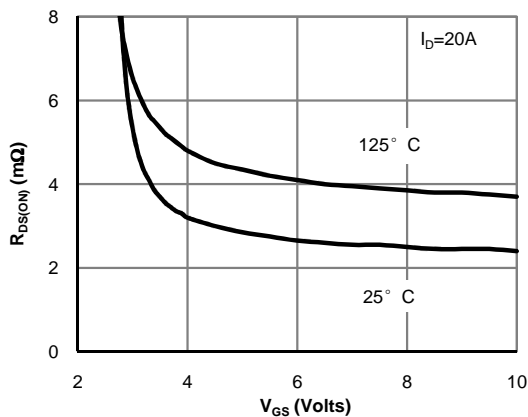
**Figure 2: Transfer Characteristics (Note E)**



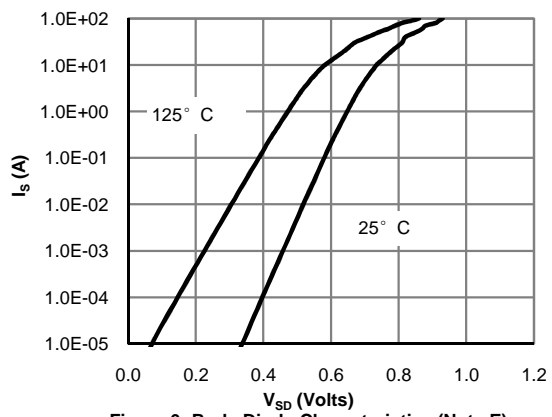
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

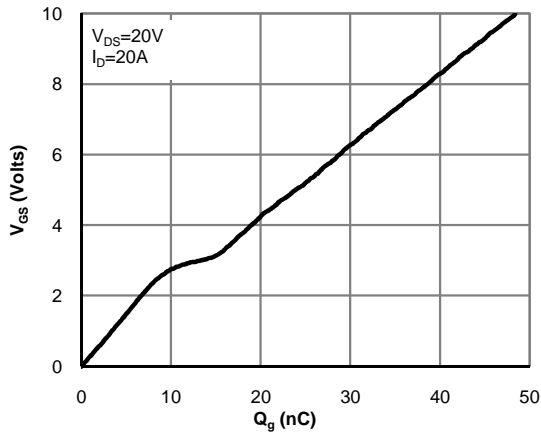


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

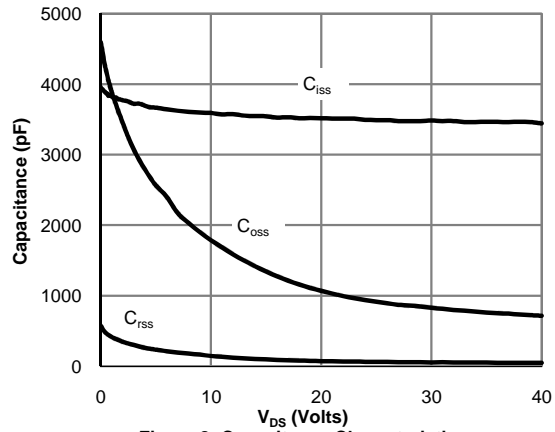


**Figure 6: Body-Diode Characteristics (Note E)**

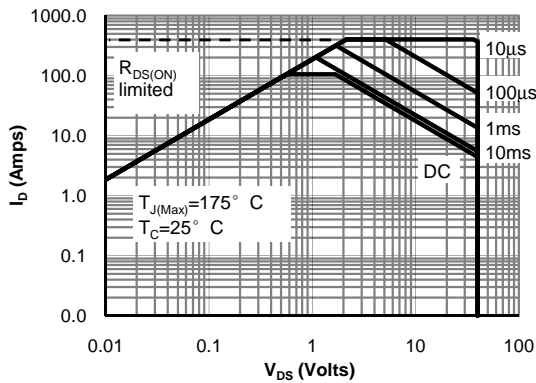
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



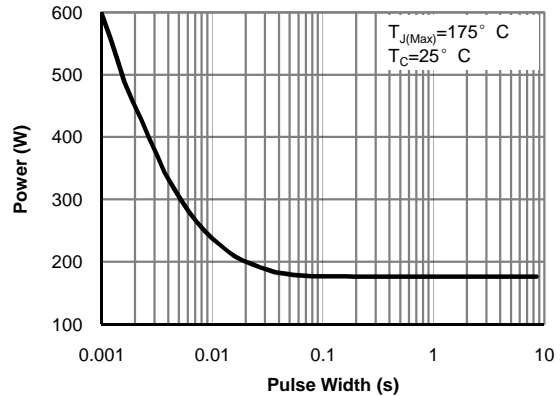
**Figure 7: Gate-Charge Characteristics**



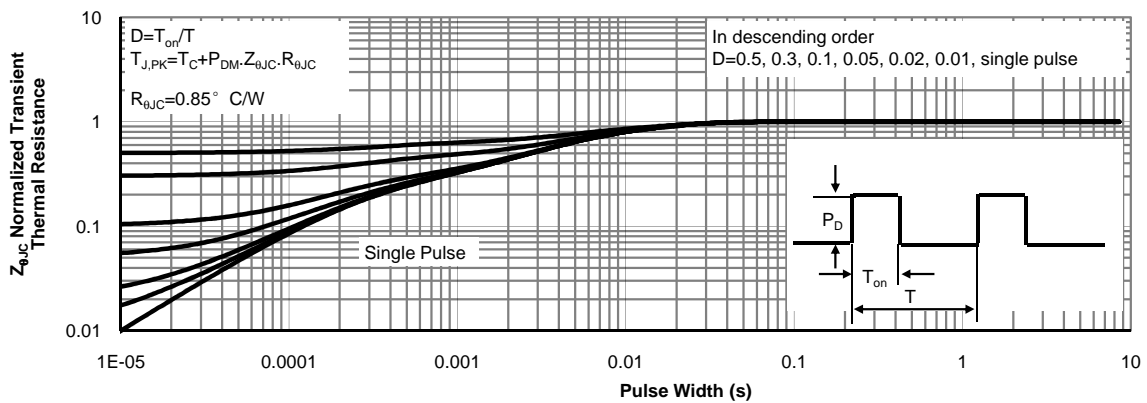
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area for AOT240L and AOB240L (Note F)**

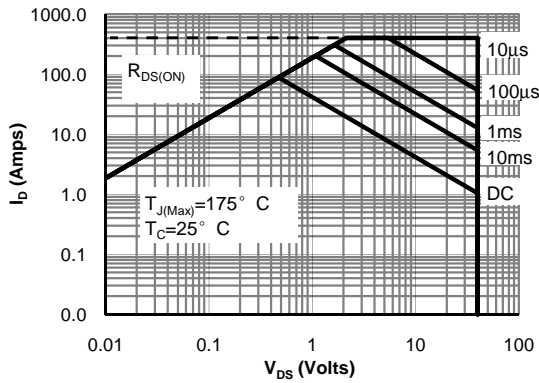


**Figure 10: Single Pulse Power Rating Junction-to-Case for AOT240L and AOB240L (Note F)**

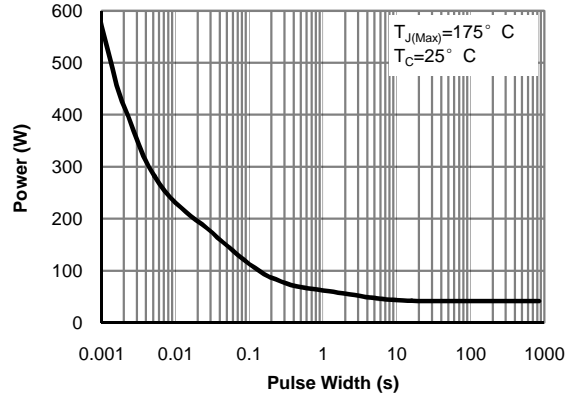


**Figure 11: Normalized Maximum Transient Thermal Impedance for AOT240L and AOB240L (Note F)**

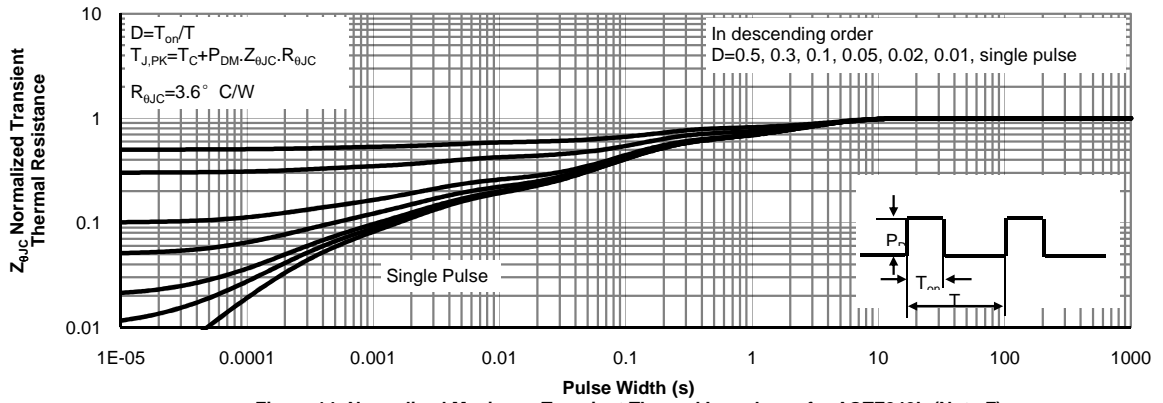
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



**Figure 12: Maximum Forward Biased Safe Operating Area for AOTF240L**

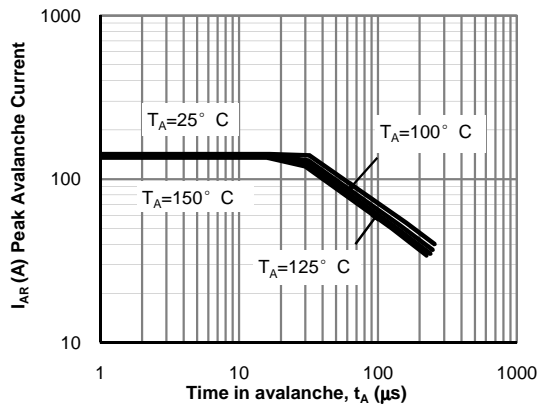


**Figure 13: Single Pulse Power Rating Junction-to-Case for AOTF240L (Note F)**

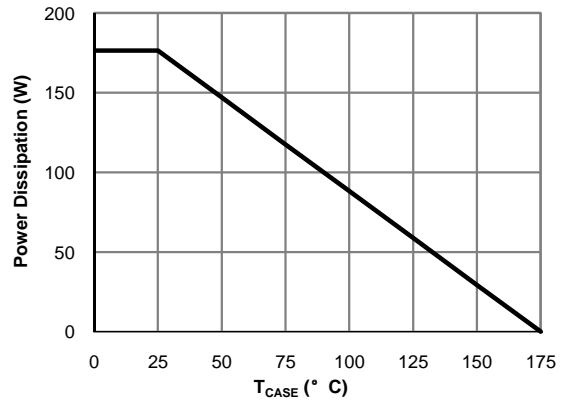


**Figure 14: Normalized Maximum Transient Thermal Impedance for AOTF240L (Note F)**

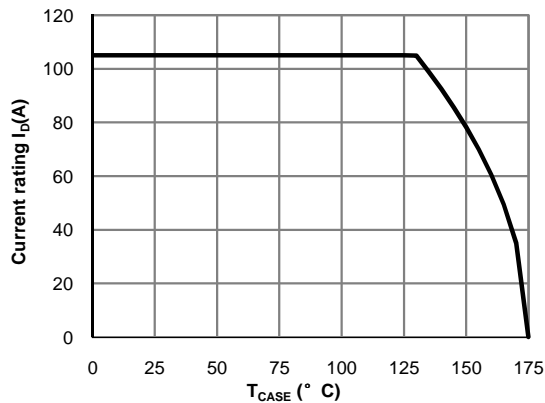
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



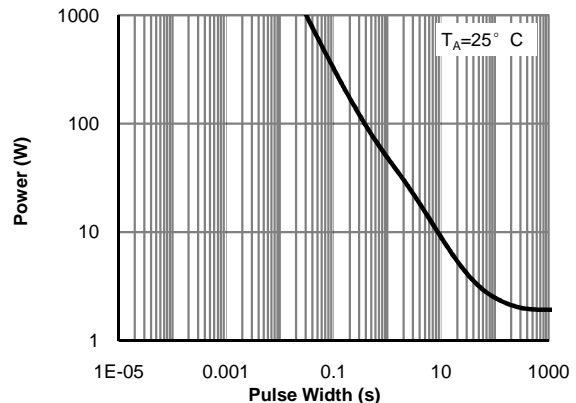
**Figure 15: Single Pulse Avalanche capability (Note C)**



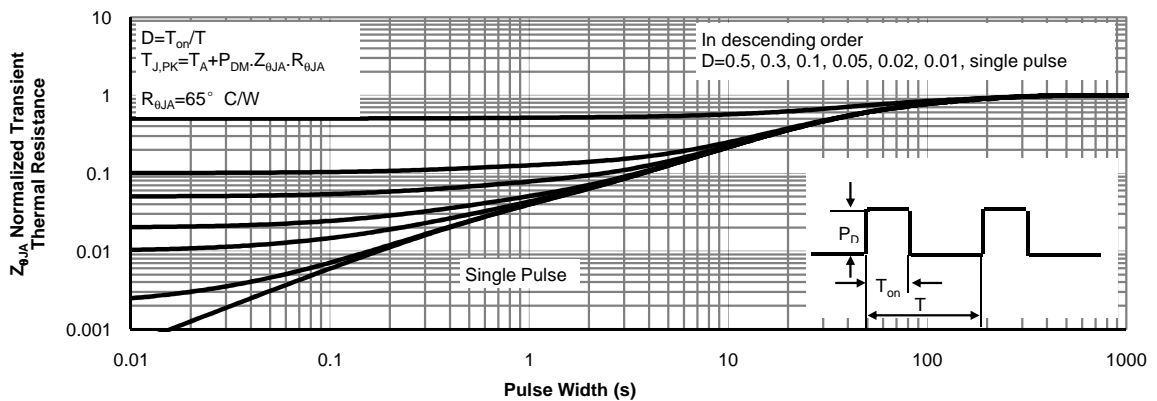
**Figure 16: Power De-rating (Note F)**



**Figure 17: Current De-rating (Note F)**



**Figure 18: Single Pulse Power Rating Junction-to-Ambient (Note H)**



**Figure 19: Normalized Maximum Transient Thermal Impedance (Note H)**

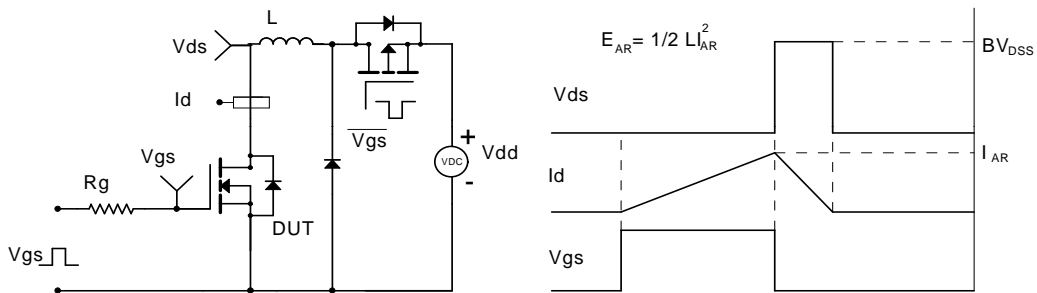
**Gate Charge Test Circuit & Waveform**



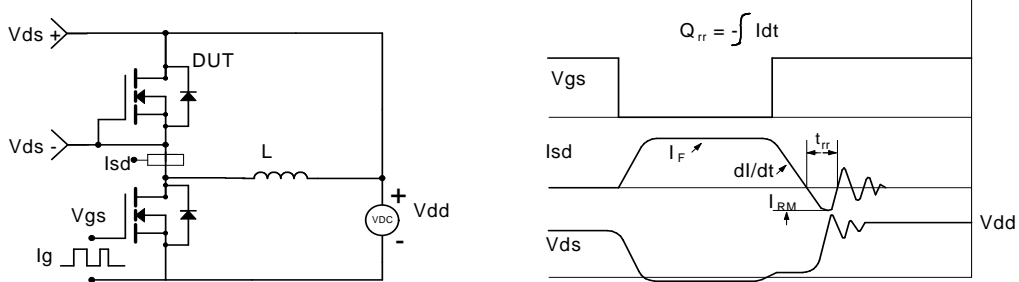
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



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